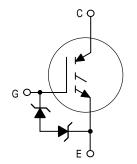
# Designer's™ Data Sheet

# **Insulated Gate Bipolar Transistor**

## N-Channel Enhancement-Mode Silicon Gate

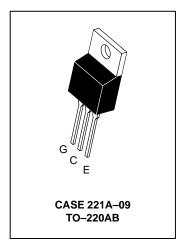
This Insulated Gate Bipolar Transistor (IGBT) uses an advanced termination scheme to provide an enhanced and reliable high voltage–blocking capability. Its new 600 V IGBT technology is specifically suited for applications requiring both a high temperature short circuit capability and a low VCE(on). It also provides fast switching characteristics and results in efficient operation at high frequencies. This new E–series introduces an energy efficient, ESD protected, and short circuit rugged device.

- Industry Standard TO-220 Package
- High Speed: E<sub>off</sub> = 60 μJ/A typical at 125°C
- High Voltage Short Circuit Capability 10 μs minimum at 125°C, 400 V
- Low On-Voltage 2.0 V typical at 5.0 A, 125°C
- Robust High Voltage Termination
- ESD Protection Gate-Emitter Zener Diodes



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IGBT IN TO-220
9.0 A @ 90°C
10 A @ 25°C
600 VOLTS
SHORT CIRCUIT RATED
LOW ON-VOLTAGE



#### **MAXIMUM RATINGS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector–Emitter Voltage	VCES	600	Vdc	
Collector–Gate Voltage ( $R_{GE} = 1.0 \text{ M}\Omega$ )	VCGR	600	Vdc	
Gate-Emitter Voltage — Continuous	V <sub>GE</sub>	±20	Vdc	
Collector Current — Continuous @ T <sub>C</sub> = 25°C — Continuous @ T <sub>C</sub> = 90°C — Repetitive Pulsed Current (1)	I <sub>C25</sub> I <sub>C90</sub> I <sub>CM</sub>	10 7.0 14	Adc Apk	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	81 0.65	Watts W/°C	
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	
Short Circuit Withstand Time ( $V_{CC}$ = 400 Vdc, $V_{GE}$ = 15 Vdc, $T_J$ = 125°C, $R_G$ = 20 $\Omega$ )	t <sub>SC</sub>	10	μS	
Thermal Resistance — Junction to Case – IGBT — Junction to Ambient	R <sub>θJC</sub> R <sub>θJA</sub>	1.5 65	°C/W	
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C	
Mounting Torque, 6–32 or M3 screw	10	10 lbf•in (1.13 N•m)		

<sup>(1)</sup> Pulse width is limited by maximum junction temperature. Repetitive rating.

**Designer's Data for "Worst Case" Conditions** — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•	•
Collector–to–Emitter Breakdown (V <sub>GE</sub> = 0 Vdc, I <sub>C</sub> = 25 μAdc) Temperature Coefficient (Posit	V(BR)CES	600 —	 870	_	Vdc mV/°C	
Emitter-to-Collector Breakdown	V(BR)ECS	15	_	_	Vdc	
Zero Gate Voltage Collector Curr (V <sub>CE</sub> = 600 Vdc, V <sub>GE</sub> = 0 Vdc (V <sub>CE</sub> = 600 Vdc, V <sub>GE</sub> = 0 Vdc	ICES	_	_	10 200	μAdc	
Gate-Body Leakage Current (Vo	IGES	_	_	50	μAdc	
ON CHARACTERISTICS (1)		•		•	•	
Collector-to-Emitter On-State V (VGE = 15 Vdc, IC = 2.5 Adc) (VGE = 15 Vdc, IC = 2.5 Adc, (VGE = 15 Vdc, IC = 5.0 Adc,	VCE(on)	_ _ _	1.6 1.5 2.0	1.9 — 2.4	Vdc	
Gate Threshold Voltage (V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1.0 mAdc) Threshold Temperature Coeffic	VGE(th)	4.0 —	6.0 10	8.0 —	Vdc mV/°C	
Forward Transconductance (VCE	9fe	_	2.5	_	Mhos	
DYNAMIC CHARACTERISTICS		•		•		
Input Capacitance		C <sub>ies</sub>	_	610	_	pF
Output Capacitance	(V <sub>CE</sub> = 25 Vdc, V <sub>GE</sub> = 0 Vdc, f = 1.0 MHz)	C <sub>oes</sub>	_	60	_	
Transfer Capacitance	- ,	C <sub>res</sub>	_	10	_	
SWITCHING CHARACTERISTICS	5 (1)					
Turn-On Delay Time		<sup>t</sup> d(on)	_	22	_	ns
Rise Time	$(V_{CC} = 360 \text{ Vdc}, I_{C} = 5.0 \text{ Adc},$	t <sub>r</sub>	_	24	_	
Turn-Off Delay Time	V <sub>GE</sub> = 15 Vdc, L = 300 μH, R <sub>G</sub> = 20 Ω, T <sub>J</sub> = 25°C)	td(off)	_	64	_	
Fall Time	Energy losses include "tail"	tf	_	196	_	
Turn-Off Switching Loss	7	E <sub>off</sub>	_	0.20	0.34	mJ
Turn-On Delay Time		<sup>t</sup> d(on)	_	31	_	ns
Rise Time	(V <sub>CC</sub> = 360 Vdc, I <sub>C</sub> = 5.0 Adc,	t <sub>r</sub>	_	24	_	
Turn-Off Delay Time	V <sub>GE</sub> = 15 Vdc, L = 300 μH, R <sub>G</sub> = 20 $\Omega$ , T <sub>J</sub> = 125°C)	t <sub>d</sub> (off)	_	195	_	
Fall Time	Energy losses include "tail"	tf	_	220	<u> </u>	
Turn-Off Switching Loss	7	E <sub>off</sub>	_	0.38	_	mJ
Gate Charge	(V <sub>CC</sub> = 360 Vdc, I <sub>C</sub> = 5.0 Adc, V <sub>GE</sub> = 15 Vdc)	QT	_	27.2	_	nC
		Q <sub>1</sub>	_	7.0	_	
	- GE - 10 Vao,	Q <sub>2</sub>	_	13.7	_	
NTERNAL PACKAGE INDUCTA	ICE		-	-	-	-
Internal Emitter Inductance (Measured from the emitter lea	LE	_	7.5	_	nH	

<sup>(1)</sup> Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

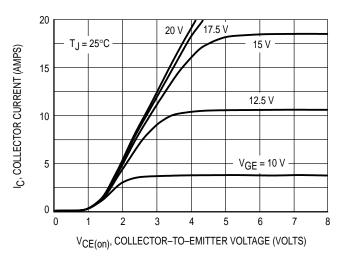


Figure 1. Output Characteristics

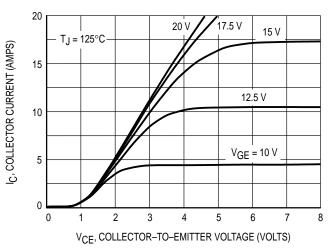


Figure 2. Output Characteristics

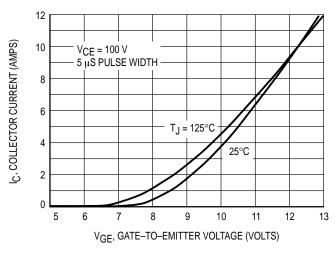


Figure 3. Transfer Characteristics

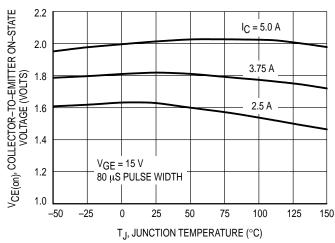


Figure 4. V<sub>CE</sub> versus Junction Temperature

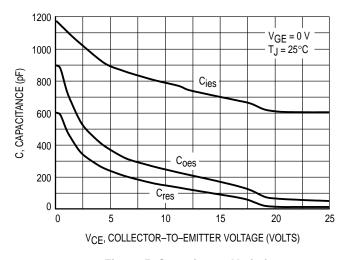


Figure 5. Capacitance Variation

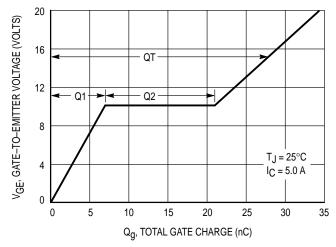


Figure 6. VGE versus Total Charge

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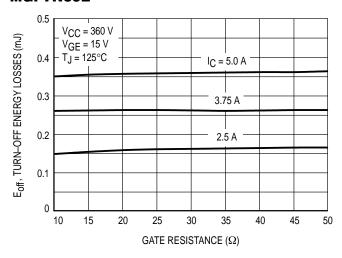


Figure 7. Turn-Off Losses versus Gate Resistance

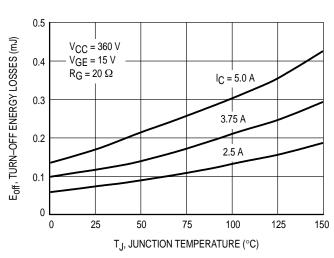


Figure 8. Turn-Off Losses versus Junction Temperature

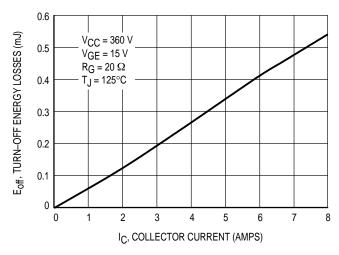


Figure 9. Turn-Off Energy Losses versus Collector Current

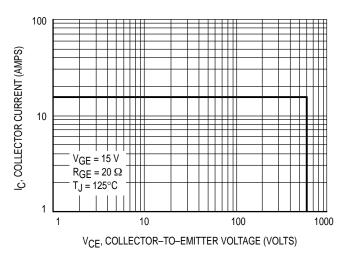
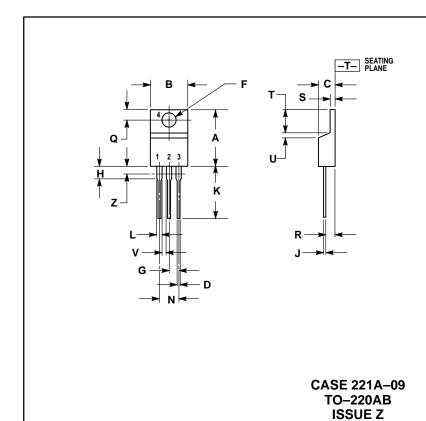


Figure 10. Reverse Biased Safe Operating Area

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#### **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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